

33. (Amended) A magnetic device, comprising:

an first electrode layer including a first magnetic material;

an insulating layer on the first electrode layer; and

a second electrode layer including at least one magnetic material, wherein the second electrode layer comprises a basic layer on the insulating layer and a layer structure on the basic layer, wherein the basic layer includes a central portion and a peripheral portion, wherein the central portion and the peripheral portion are each in direct mechanical contact with the insulating layer, wherein the peripheral portion circumscribes the central portion and is integral with the central portion, wherein the thickness of the peripheral portion is less than the thickness of the central portion, and wherein the layer structure effectuates a magnetic pinning of the basic layer.

34. (Amended) The magnetic device of claim 33, wherein the insulating layer comprises a non-magnetic material element, and wherein the mass of the non-magnetic element is less than the mass of a metallic element of the second magnetic material.

35. (Amended) The magnetic device of claim 33, wherein the first magnetic material comprises a first soft-magnetic material.

36. (Amended) The magnetic device of claim 35, wherein the at least one magnetic material comprises:

a second soft-magnetic material in the central portion of the basic layer;

the second soft-magnetic material in the peripheral portion basic layer; and

an anti-ferromagnetic material in the layer structure.

37. (Amended) The magnetic device of claim 35, wherein the at least one magnetic material comprises:

- a second soft-magnetic material in the central portion of the basic layer;
- the second soft-magnetic material in the peripheral portion basic layer; and
- a hard-magnetic material in the layer structure.

39. (Amended) The magnetic device of claim 35, wherein the at least one magnetic material comprises:

- a ferromagnetic material in the central portion of the basic layer; and
- the ferromagnetic material in the peripheral portion basic layer.

42. (Amended) The magnetic device of claim 35, wherein the basic layer comprises a ferromagnetic material, and wherein the layer structure comprises an artificial anti-ferromagnetic structure comprising two anti-parallel magnetic layers separated by a metallic intermediate layer.

43. (Amended) The magnetic device of claim 33, further comprising a protective layer of insulative material on the insulating layer, wherein the protective layer circumscribes the basic layer, and wherein the protective layer is in direct mechanical contact with the basic layer and with the insulating layer.

44. (Amended) The magnetic device of claim 43, wherein the thickness of the protective layer is less than the thickness of the second electrode layer.

45. (Amended) A magnetic device, comprising:

- an first electrode layer including a first magnetic material;

an insulating layer on the first electrode layer, wherein the insulating layer comprises a non-magnetic material element;

a second electrode layer including at least one magnetic material, wherein the second electrode layer is on a first portion of the insulating layer and is not on a second portion of the insulating layer, and wherein the mass of the non-magnetic element is less than the mass of a metallic element of the at least one magnetic material; and

a magnetic yoke in magnetic contact with the first electrode layer.

46. (Amended) The magnetic device of claim 45, wherein the magnetic yoke comprises an interruption that includes an insulating material, and wherein the interruption directly contacts a portion of a surface of the first electrode layer.

47. (Amended) The magnetic device of claim 46, wherein the magnetic yoke further comprises a non-magnetic transducing gap that includes the insulating material.

48. (New) The magnetic device of claim 45, further comprising a protective layer of insulative material on the insulating layer, wherein the protective layer circumscribes the second electrode layer, wherein the protective layer is in direct mechanical contact with both the insulating layer and the second electrode layer, and wherein the thickness of the protective layer is less than the thickness of the second electrode layer.

49. (New) The magnetic device of claim 45, wherein the second electrode layer comprises a basic layer on the insulating layer and a layer structure on the basic layer, wherein the basic layer is in direct mechanical contact with the insulating layer, and wherein the layer structure effectuates a magnetic pinning of the basic layer.